

DRAM MODULE

2 MEG x 32 DRAM FAST PAGE MODE

DRAM MODULE

FEATURES

- Industry standard pinout in a 72-pin single-in-line package
- High-performance, CMOS silicon gate process.
- Single 5V ±10% power supply
- All inputs, outputs and clocks are fully TTL and CMOS compatible
- Low power, 48mW standby; 3600mW active, typical
- Refresh modes: $\overline{\text{RAS}}$ -ONLY, $\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ and HIDDEN
- 1,024-cycle refresh distributed across 16ms
- Optional FAST PAGE MODE access cycle

OPTIONS

- Timing
 - 70ns access
 - 80ns access
 - 100ns access

MARKING

- Packages
 - Leadless 72-pin SIMM M
 - Leadless 72-pin SIMM (Gold) G
 - Leaded 72-pin ZIP Z

PIN ASSIGNMENT (Top View)

72-Pin SIMM (I-6)

72-Pin ZIP (J-5)

PIN #	SYMBOL	PIN#	SYMBOL	PIN#	SYMBOL	PIN#	SYMBOL
1	Vss	19	NC	37	NC	55	DQ12
2	DQ1	20	DQ5	38	NC	56	DQ28
3	DQ17	21	DQ21	39	Vss	57	DQ13
4	DQ2	22	DQ6	40	CAS0	58	DQ29
5	DQ18	23	DQ22	41	CAS2	59	Vcc
6	DQ3	24	DQ7	42	CAS3	60	DQ30
7	DQ19	25	DQ23	43	CAS1	61	DQ14
8	DQ4	26	DQ8	44	RAS0	62	DQ31
9	DQ20	27	DQ24	45	RAS1	63	DQ15
10	Vcc	28	A7	46	NC	64	DQ32
11	NC	29	NC	47	WE	65	DQ16
12	A0	30	Vcc	48	NC	66	NC
13	A1	31	A8	49	DQ9	67	PRD1
14	A2	32	A9	50	DQ25	68	PRD2
15	A3	33	RAS3	51	DQ10	69	PRD3
16	A4	34	RAS2	52	DQ26	70	PRD4
17	A5	35	NC	53	DQ11	71	NC
18	A6	36	NC	54	DQ27	72	Vss

GENERAL DESCRIPTION

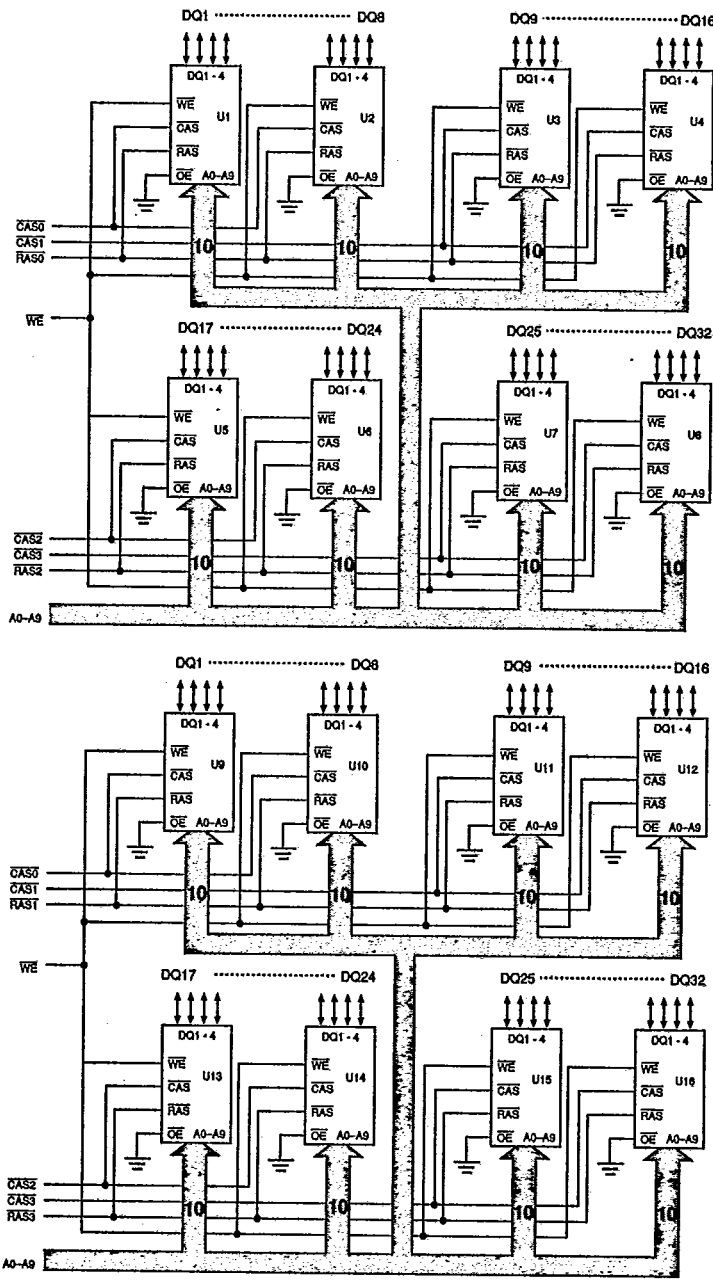
The MT16D232 is a randomly accessed solid-state memory containing 2,097,152 words organized in a x32 configuration. During READ or WRITE cycles each bit is uniquely addressed through the 20 address bits, which are entered 10 bits (A0-A9) at a time. $\overline{\text{RAS}}$ is used to latch the first 10 bits and $\overline{\text{CAS}}$ the latter 10 bits. A READ or WRITE cycle is selected with the $\overline{\text{WE}}$ input. A logic HIGH on $\overline{\text{WE}}$ dictates READ mode while a logic LOW on $\overline{\text{WE}}$ dictates WRITE mode. During a WRITE cycle, data-in (D) is latched by the falling edge of $\overline{\text{WE}}$ or $\overline{\text{CAS}}$, whichever occurs last. EARLY-WRITE occurs when $\overline{\text{WE}}$ goes LOW prior to $\overline{\text{CAS}}$ going LOW, the output pin(s) remain open (High-Z) until the next $\overline{\text{CAS}}$ cycle.

FAST PAGE MODE operations allow faster data operations (READ or WRITE) within a row-address (A0-A9) defined page boundary. The FAST PAGE MODE cycle is always initiated with a row address strobed-in by $\overline{\text{RAS}}$ followed by a column address strobed-in by $\overline{\text{CAS}}$. $\overline{\text{CAS}}$ may

be toggled-in by holding $\overline{\text{RAS}}$ LOW and strobing-in different column addresses, thus executing faster memory cycles. Returning $\overline{\text{RAS}}$ HIGH terminates the FAST PAGE MODE operation.

Returning $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ HIGH terminates a memory cycle and decreases chip current to a reduced standby level. Also, the chip is preconditioned for the next cycle during the $\overline{\text{RAS}}$ high time. Memory cell data is retained in its correct state by maintaining power and executing any $\overline{\text{RAS}}$ cycle (READ, WRITE, $\overline{\text{RAS}}$ -ONLY, $\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$, or HIDDEN REFRESH) so that all 1,024 combination of $\overline{\text{RAS}}$ addresses (A0-A9) are executed at least every 16ms, regardless of sequence.

FUNCTIONAL BLOCK DIAGRAM



U1-U16 = MT4C4001DJ

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TRUTH TABLE

Function	RAS	CAS	WE	Addresses		DQ1-32	
				'R	'C		
Standby	H	X	X	X	X	High Impedance	
READ	L	L	H	ROW	COL	Valid Data Out	
EARLY-WRITE	L	L	L	ROW	COL	Valid Data In	
FAST-PAGE-MODE READ	1st Cycle	L	H→L	H	ROW	COL	Valid Data Out
	2nd Cycle	L	H→L	H	n/a	COL	Valid Data Out
FAST-PAGE-MODE WRITE	1st Cycle	L	H→L	L	ROW	COL	Valid Data In
	2nd Cycle	L	H→L	L	n/a	COL	Valid Data In
RAS-ONLY REFRESH	L	H	X	ROW	n/a	High Impedance	
HIDDEN REFRESH	READ	L→H→L	L	H	ROW	COL	Valid Data Out
	WRITE	L→H→L	L	L	ROW	COL	Valid Data In
CAS-BEFORE-RAS REFRESH	H→L	L	X	X	X	High Impedance	

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PRESENCE DETECT

SYMBOL	-7	-8	-10
PRD1	NC	VSS	NC
PRD2	NC	VSS	NC
PRD3	VSS	VSS	NC
PRD4	NC	NC	NC

ABSOLUTE MAXIMUM RATINGS*

Voltage on Vcc supply relative to Vss-1.0V to +7.0V
 Operating Temperature, TA(Ambient)0°C to +70°C
 Storage Temperature (Plastic)-55°C to +150°C
 Power Dissipation16W
 Short Circuit Output Current50mA

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

ELECTRICAL CHARACTERISTICS AND RECOMMENDED DC OPERATING CONDITIONS

(Notes: 1, 3, 4, 6, 7) ($0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$; $V_{CC} = 5.0\text{V} \pm 10\%$)

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PARAMETER/CONDITION	SYMBOL	MIN	MAX	UNITS	NOTES
Supply Voltage	V_{CC}	4.5	5.5	V	
Input High (Logic 1) Voltage, All Inputs	V_{IH}	2.4	$V_{CC}+1$	V	1
Input Low (Logic 0) Voltage, All Inputs	V_{IL}	-1.0	0.8	V	1
INPUT LEAKAGE CURRENT Any Input $0\text{V} \leq V_{IN} \leq V_{CC}$ (All other pins not under test = 0V) For each package input	A0-A9, WE I_i	-32	32	μA	
OUTPUT LEAKAGE CURRENT (Q is disabled, $0\text{V} \leq V_{OUT} \leq V_{CC}$) For each package input	DQ1-DQ32 I_{OZ}	-24	24	μA	
OUTPUT LEVELS Output High Voltage ($I_{OH} = -5\text{mA}$) Output Low Voltage ($I_{OL} = 5\text{mA}$)	V_{OH} V_{OL}	2.4	0.4	V	1

PARAMETER/CONDITION	SYMBOL	MAX			UNITS	NOTES
		-7	-8	-10		
OPERATING CURRENT ($\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ = Cycling; $t_{RC} = t_{RC}(\text{MIN})$)	I_{CC1}	816	736	656	mA	2
OPERATING CURRENT: FAST PAGE MODE ($\overline{\text{RAS}} = V_{IL}$, $\overline{\text{CAS}}$ = Cycling; $t_{PC} = t_{PC}(\text{MIN})$)	I_{CC2}	576	496	416	mA	2
STANDBY CURRENT: TTL INPUT LEVELS Power supply standby current ($\overline{\text{RAS}} = \overline{\text{CAS}} = V_{IH}$ after 8 $\overline{\text{RAS}}$ cycles (MIN))	I_{CC3}	32	32	32	mA	
STANDBY CURRENT: CMOS INPUT LEVELS Power supply standby current ($\overline{\text{RAS}} = \overline{\text{CAS}} = V_{CC} - 0.2\text{V}$ after 8 $\overline{\text{RAS}}$ cycles (MIN)). (All other inputs at $V_{CC} - 0.2\text{V}$ or $V_{SS} + 0.2\text{V}$)	I_{CC4}	16	16	16	mA	
REFRESH CURRENT: $\overline{\text{RAS}}$ -ONLY ($\overline{\text{RAS}}$ = Cycling; $\overline{\text{CAS}} = V_{IH}$)	I_{CC5}	816	736	656	mA	2
REFRESH CURRENT: $\overline{\text{CAS}}$ -BEFORE- $\overline{\text{RAS}}$ ($\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ = Cycling)	I_{CC6}	816	736	656	mA	2

CAPACITANCE

PARAMETER	SYMBOL	MIN	MAX	UNITS	NOTES
Input Capacitance: A0-A9	C_{I1}		80	pF	17
Input Capacitance: WE	C_{I2}		112	pF	17
Input Capacitance: $\overline{\text{CAS0}}$ - $\overline{\text{CAS3}}$, $\overline{\text{RAS0}}$ - $\overline{\text{RAS3}}$	C_{I4}		28	pF	17
Input/Output Capacitance: DQ1-DQ32	C_{IO}		14	pF	17

MICRON

MT16D232

T-46-23-17

ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

(Notes: 3, 4, 5, 10, 11, 16, 17) ($0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$; $V_{CC} = 5.0\text{V} \pm 10\%$)

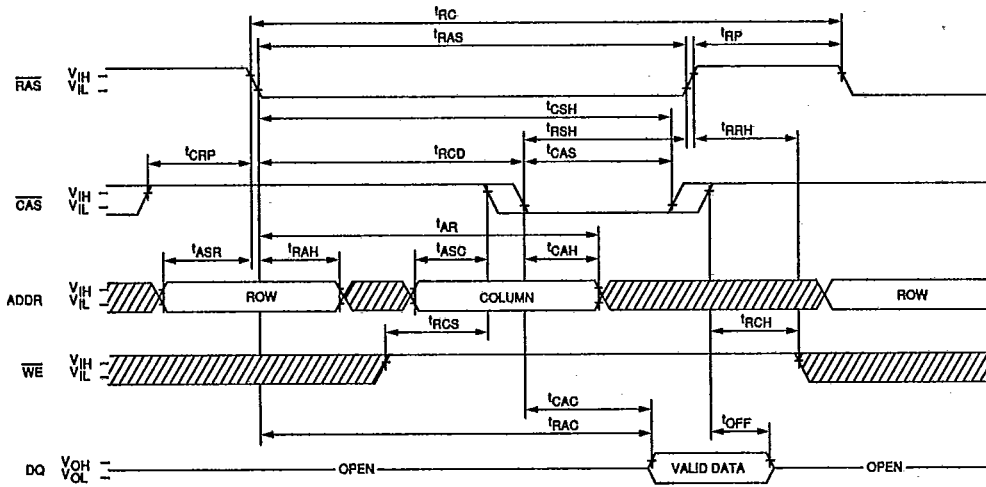
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A.C. CHARACTERISTICS	SYM	-7		-8		-10		UNITS	NOTES
PARAMETER		MIN	MAX	MIN	MAX	MIN	MAX		
Random READ or WRITE cycle time	t_{RC}	130		150		180		ns	6, 7
FAST-PAGE-MODE cycle time	t_{PC}	40		45		55		ns	6, 7
Access time from RAS	t_{RAC}		70		80		100	ns	7, 8
Access time from $\overline{\text{CAS}}$	t_{CAC}		20		20		25	ns	7, 9
RAS pulse width	t_{RAS}	70	100,000	80	100,000	100	100,000	ns	
RAS hold time	t_{RSH}	20		20		25		ns	
RAS precharge time	t_{RP}	50		60		70		ns	
$\overline{\text{CAS}}$ pulse width	t_{CAS}	20	100,000	20	100,000	25	100,000	ns	
$\overline{\text{CAS}}$ hold time	t_{CSH}	70		80		100		ns	
$\overline{\text{CAS}}$ precharge time	t_{CPN}	10		10		15		ns	18
$\overline{\text{CAS}}$ precharge time (FAST PAGE MODE)	t_{CP}	10		10		10		ns	
RAS to $\overline{\text{CAS}}$ delay time	t_{RCD}	20	50	20	60	25	75	ns	13
$\overline{\text{CAS}}$ to RAS setup time	t_{CRP}	5		5		20		ns	
Row address setup time	t_{ASR}	0		0		0		ns	
Row address hold time	t_{RAH}	10		10		15		ns	
Column address setup time	t_{ASC}	0		0		0		ns	
Column address hold time	t_{CAH}	15		15		20		ns	
Column address hold time referenced to RAS	t_{AR}	55		60		70		ns	
Read command setup time	t_{RCS}	0		0		0		ns	
Read command hold time referenced to $\overline{\text{CAS}}$	t_{RCH}	0		0		0		ns	14
Read command hold time referenced to RAS	t_{RRH}	0		0		0		ns	
Output buffer turn-off delay	t_{OFF}	0	20	0	20	0	20	ns	12
$\overline{\text{WE}}$ command setup time	t_{WCS}	0		0		0		ns	
Write command hold time	t_{WCH}	15		15		20		ns	
Write command hold time referenced to RAS	t_{WCR}	55		60		75		ns	
Write command pulse width	t_{WP}	15		15		20		ns	
Write command to RAS lead time	t_{RWL}	15		20		25		ns	
Write command to $\overline{\text{CAS}}$ lead time	t_{CWL}	15		20		25		ns	
Data-in setup time	t_{DS}	0		0		0		ns	15
Data-in hold time	t_{DH}	15		15		20		ns	15
Data-in hold time referenced to RAS	t_{DHR}	55		60		75		ns	
Transition time (rise or fall)	t_T	3	50	3	50	3	50	ns	16
Refresh period (256 cycles)	t_{REF}		16		16		16	ms	20
$\overline{\text{CAS}}$ hold time (CAS-BEFORE-RAS REFRESH)	t_{CHR}	15		15		15		ns	19
$\overline{\text{CAS}}$ set-up time (CAS-BEFORE-RAS REFRESH)	t_{CSR}	10		10		10		ns	19
RAS to $\overline{\text{CAS}}$ precharge time	t_{RPC}	0		0		0		ns	19

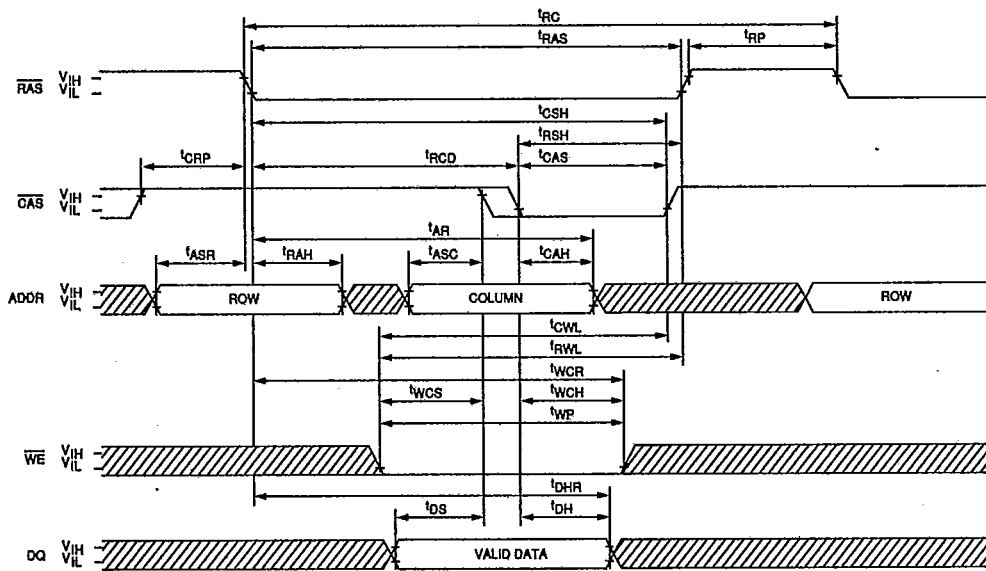
NOTES



1. All voltages referenced to V_{SS} .
2. I_{CC} is dependent on output loading and cycle rates. Specified values are obtained with minimum cycle time and the output open.
3. An initial pause of 100 μ s is required after power-up followed by eight \overline{RAS} REFRESH cycles (\overline{RAS} -ONLY or CBR with \overline{WE} HIGH) before proper device operation is assured. The eight \overline{RAS} cycle wake-up should be repeated any time the 16ms refresh requirement is exceeded.
4. AC characteristics assume $t_T = 5$ ns.
5. V_{IH} (MIN) and V_{IL} (MAX) are reference levels for measuring timing of input signals. Transition times are measured between V_{IH} and V_{IL} .
6. The minimum specifications are used only to indicate cycle time at which proper operation over the full temperature range ($0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$) is assured.
7. Measured with a load equivalent to two TTL gates and 100pF.
8. Assumes that $t_{RCD} < t_{RCD}(\text{MAX})$. If t_{RCD} is greater than the maximum recommended value shown in this table, t_{RAC} will increase by the amount that t_{RCD} exceeds the value shown.
9. Assumes that $t_{RCD} \geq t_{RCD}(\text{MAX})$.
10. If $\overline{CAS} = V_{IH}$, data output is high impedance.
11. If $\overline{CAS} = V_{IL}$, data output may contain data from the last valid READ cycle.
12. $t_{OFF}(\text{MAX})$ defines the time at which the output achieves the open circuit condition and is not referenced to V_{OH} or V_{OL} .
13. Operation within the $t_{RCD}(\text{MAX})$ limit ensures that $t_{RAC}(\text{MAX})$ can be met. $t_{RCD}(\text{MAX})$ is specified as a reference point only; if t_{RCD} is greater than the specified $t_{RCD}(\text{MAX})$ limit, then access time is controlled exclusively by t_{CAC} .
14. t_{RCH} is referenced to the first rising edge of \overline{RAS} or \overline{CAS} .
15. These parameters are referenced to \overline{CAS} leading edge in EARLY-WRITE cycles.
16. In addition to meeting the transition rate specification, all input signals must transit between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}) in a monotonic manner.
17. This parameter is sampled. Capacitance is calculated from the equation $C = I^{di}/dv$ with $dv = 3\text{V}$ and $V_{CC} = 5\text{V}$.
18. If \overline{CAS} is LOW at the falling edge of \overline{RAS} , data-out (Q) will be maintained from the previous cycle. To initiate a new cycle and clear the data-out buffer, \overline{CAS} must be pulsed HIGH for t_{CP} . Note 8 applies to determine valid data out.
19. On-chip refresh and address counters are enabled.
20. A HIDDEN REFRESH may also be performed after a WRITE cycle. In this case, $\overline{WE} = \text{LOW}$.
21. LATE-WRITE, READ-WRITE or READ-MODIFY-WRITE cycles are not available due to \overline{OE} being grounded on U1-U16.

READ CYCLE



EARLY-WRITE CYCLE

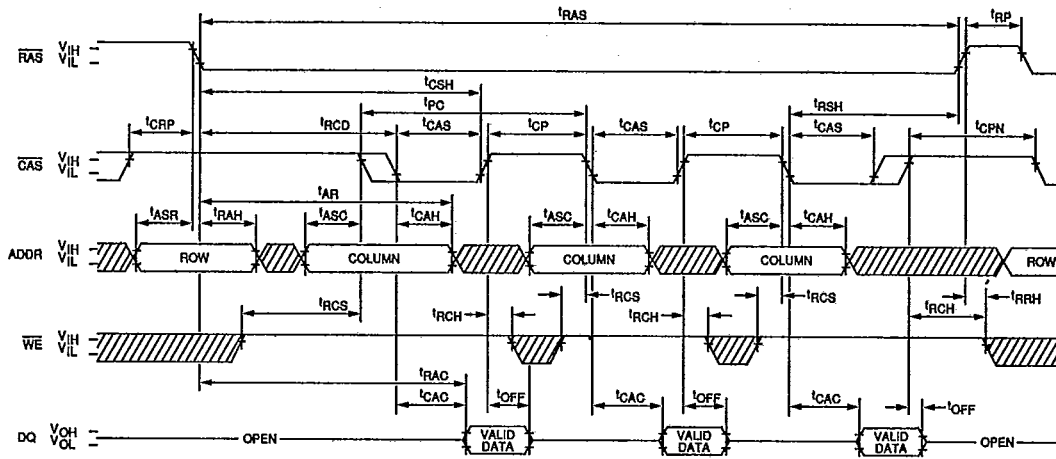


 DON'T CARE
 UNDEFINED

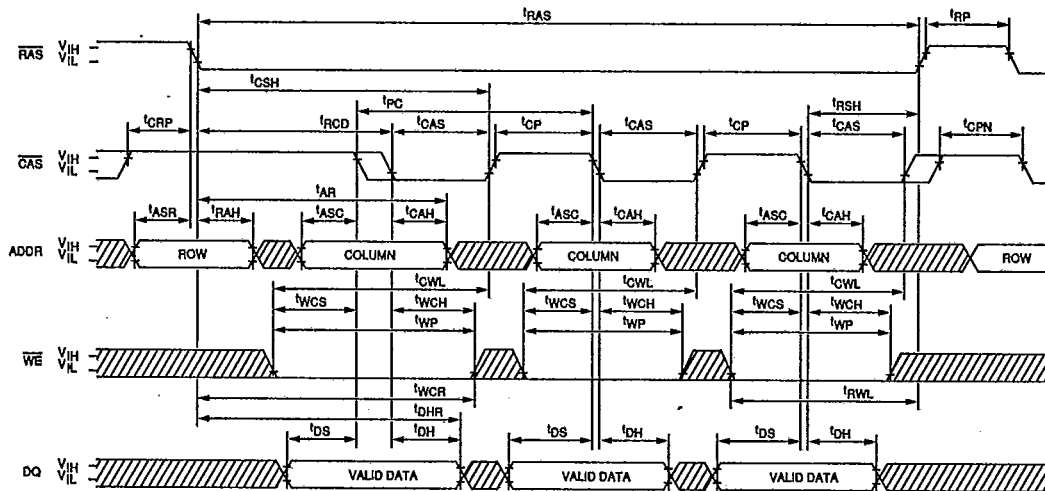
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FAST-PAGE-MODE READ CYCLE



FAST-PAGE-MODE EARLY-WRITE CYCLE



DON'T CARE
 UNDEFINED

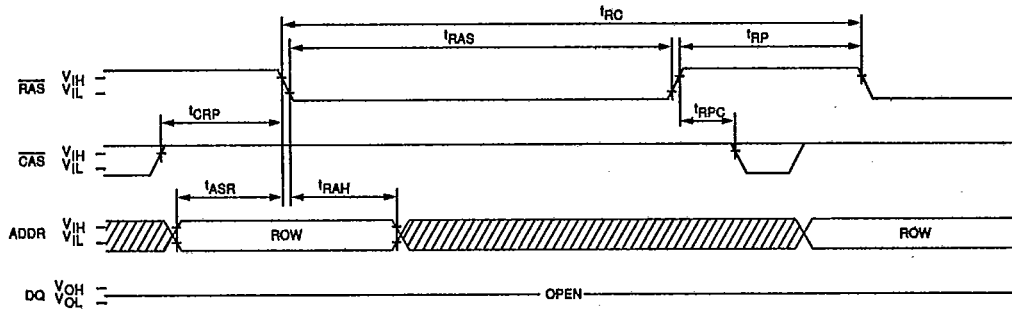
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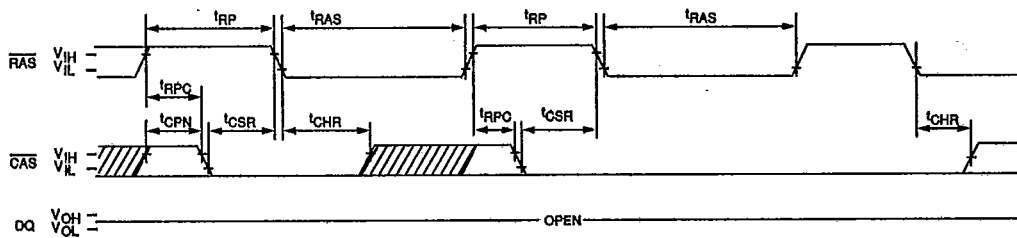
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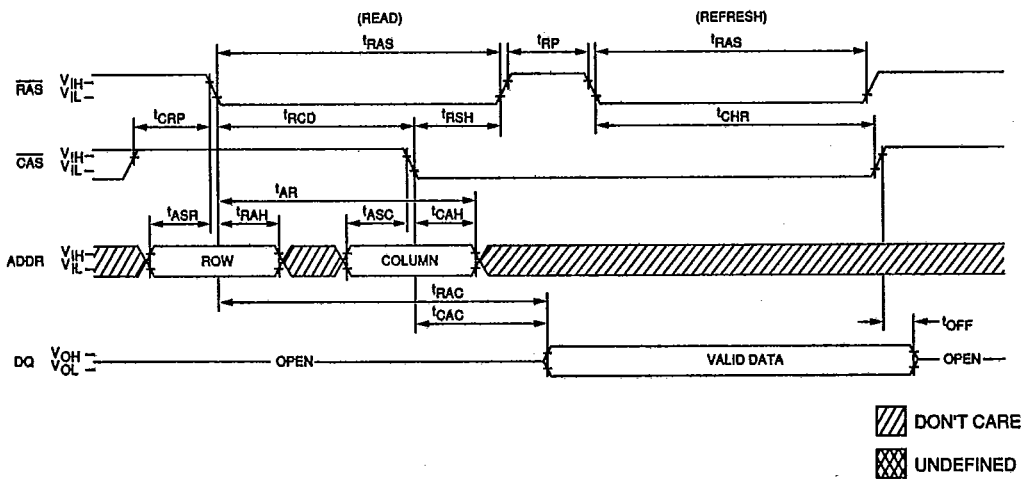
RAS-ONLY REFRESH CYCLE
(ADDR = A₀ - A₉; WE = DON'T CARE)



CAS-BEFORE-RAS REFRESH CYCLE
(A₀ - A₉, WE = DON'T CARE)



HIDDEN REFRESH CYCLE
(WE = HIGH)²⁰



DONT CARE
 UNDEFINED

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